

## **isc** Silicon NPN Power Transistor

# 2SC4027

#### DESCRIPTION

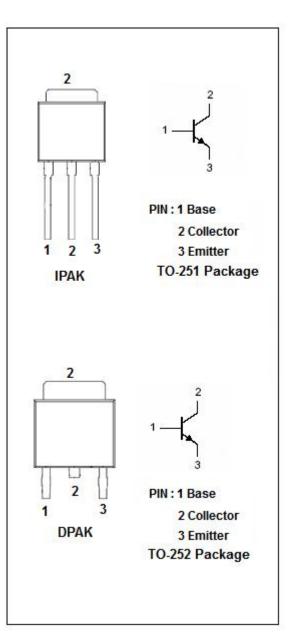
- High voltage and large current capacity
- Ultrahigh-speed switching
- Small and slim package permitting
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation
- Complementary to 2SA1552

#### **APPLICATIONS**

• Converters , inverters and color TV audio output

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
Vсво	Collector-Base Voltage 180		V	
V <sub>CEO</sub>	Collector-Emitter Voltage	160	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	V	
lc	Collector Current-Continuous	1.5	A	
Ісм	Collector Current-Peak	2.5	A	
Pc	Collector Power Dissipation @ $T_c=25^{\circ}$	15	W	
	Collector Power Dissipation @Ta=25°C	1.0		
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	T <sub>stg</sub> Storage Temperature Range		°C	





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### ELECTRICAL CHARACTERISTICS

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 0.5A; I <sub>B</sub> = 50mA			0.45	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I <sub>C</sub> = 0.5A; I <sub>B</sub> = 50mA			1.2	V
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10uA; I <sub>B</sub> = 0	180			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10uA; I <sub>C</sub> = 0	6			V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 120V; I <sub>E</sub> = 0			1.0	μA
Іево	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0			1.0	μA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	100		400	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 10mA; V <sub>CE</sub> = 5V	80			
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f= 1.0MHz		12		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 50mA; V <sub>CE</sub> = 10V		120		MHz

#### • h<sub>FE-1</sub> Classifications

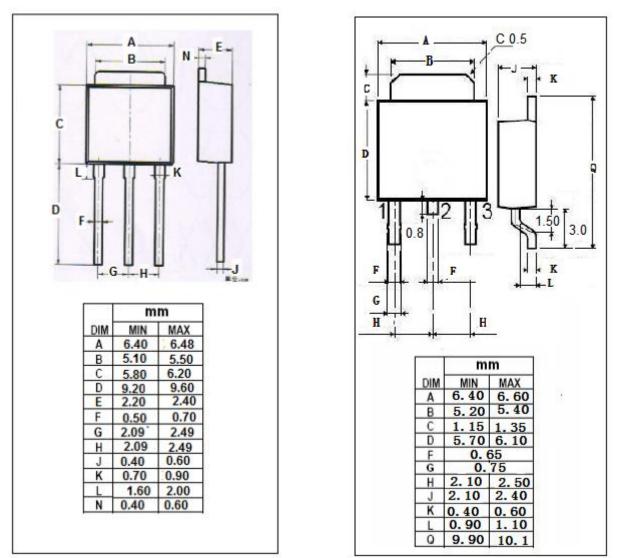
R	S	Т
100-200	140-280	200-400



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### **Outline Drawing**



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